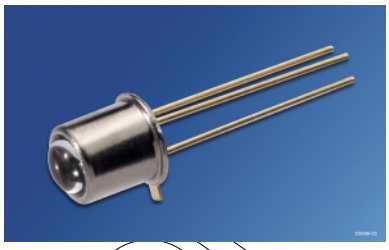
NPN-Silizium-Fototransistor
Silicon NPN Phototransistor

BPY 62



Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 420 nm bis 1130 nm
- Hohe Linearität
- Hermetisch dichte Metallbauform (TO-18) mit Basisanschluß, geeignet bis 125 °C
- Gruppiert lieferbar

Anwendungen

- Lichtschranken für Gleich- und Wechsellichtbetrieb
- Industrieelektronik
- „Messen/Steuern/Regeln“

Features

- Especially suitable for applications from 420 nm to 1130 nm
- High linearity
- Hermetically sealed metal package (TO-18) with base connection, suitable up to 125 °C
- Available in groups

Applications

- Photointerrupters
- Industrial electronics
- For control and drive circuits

Typ Type	Bestellnummer Ordering Code
BPY 62	Q60215-Y62
BPY 62-3	Q60215-Y1112
BPY 62-3/4	Q60215-Y5198
BPY 62-4	Q60215-Y1113

Grenzwerte
Maximum Ratings

Bezeichnung **Parameter**	**Symbol** **Symbol**	**Wert** **Value**	**Einheit** **Unit**
Betriebs- und Lagertemperatur Operating and storage temperature range	T_{op}; T_{stg}	– 40 … + 125	°C
Löttemperatur bei Tauchlötung Lötstelle ≥ 2 mm vom Gehäuse, Lötzeit $t \leq 5$ s Dip soldering temperature ≥ 2 mm distance from case bottom, soldering time $t \leq 5$ s	T_S	260	°C
Löttemperatur bei Kolbenlötung Lötstelle ≥ 2 mm vom Gehäuse, Lötzeit $t \leq 3$ s Iron soldering temperature ≥ 2 mm distance from case bottom, soldering time $t \leq 3$ s	T_S	300	°C
Kollektor-Emitterspannung Collector-emitter voltage	V_{CE}	50	V
Kollektorstrom Collector current	I_C	100	mA
Kollektorspitzenstrom, $\tau < 10$ µs Collector surge current	I_{CS}	200	mA
Emitter-Basisspannung Emitter-base voltage	V_{EB}	7	V
Verlustleistung, $T_A = 25$ °C Total power dissipation	P_{tot}	200	mW
Wärmewiderstand Thermal resistance	R_{thJA}	500	K/W

Kennwerte (T_A = 25 °C, λ = 950 nm)
Characteristics

Bezeichnung **Parameter**	**Symbol** **Symbol**	**Wert** **Value**	**Einheit** **Unit**
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\ max}$	850	nm
Spektraler Bereich der Fotoempfindlichkeit S = 10% von S_{max} Spectral range of sensitivity S = 10% of S_{max}	λ	420 … 1130	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	0.12	mm^2
Abmessung der Chipfläche Dimensions of chip area	$L \times B$ $L \times W$	0.5 × 0.5	mm × mm
Abstand Chipoberfläche zu Gehäuseoberfläche Distance chip front to case surface	H	2.4 … 3.0	mm
Halbwinkel Half angle	φ	± 8	Grad deg.
Fotostrom der Kollektor-Basis-Fotodiode Photocurrent of collector-base photodiode E_e = 0.5 mW/cm², V_{CB} = 5 V E_v = 1000 lx, Normlicht/standard light A, V_{CB} = 5 V	 I_{PCB} I_{PCB}	 4.5 17	 µA µA
Kapazität Capacitance V_{CE} = 0 V, f = 1 MHz, E = 0 V_{CB} = 0 V, f = 1 MHz, E = 0 V_{EB} = 0 V, f = 1 MHz, E = 0	 C_{CE} C_{CB} C_{EB}	 8 11 19	 pF pF pF
Dunkelstrom Dark current V_{CE} = 35 V, E = 0	I_{CEO}	5 (≤ 100)	nA

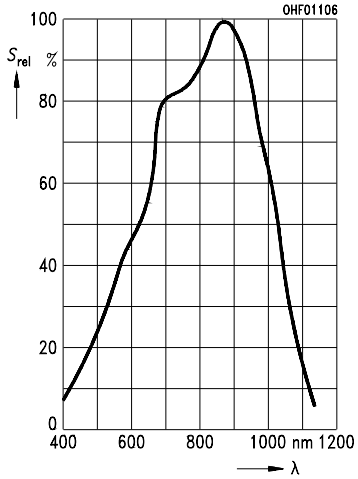
Die Fototransistoren werden nach ihrer Fotoempfindlichkeit gruppiert und mit arabischen Ziffern gekennzeichnet.
The phototransistors are grouped according to their spectral sensitivity and distinguished by arabian figures.

Bezeichnung **Parameter**	**Symbol** **Symbol**	**Wert** **Value**				**Einheit** **Unit**
		-2	**-3**	**-4**	**-5**	
Fotostrom, $\lambda = 950$ nm Photocurrent E_e = 0.5 mW/cm², V_{CE} = 5 V E_v = 1000 lx, Normlicht/ standard light A, V_{CE} = 5 V	 I_{PCE} I_{PCE}	 0.5 … 1.0 3.0	 0.8 … 1.6 4.6	 1.25 … 2.5 7.2	 ≥ 2.0 11.4	 mA mA
Anstiegszeit/Abfallzeit Rise and fall time I_C = 1 mA, V_{CC} = 5 V, R_L = 1 kΩ	t_r, t_f	5	7	9	12	µs
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage $I_C = I_{PCEmin}$ [1] × 0.3, E_e = 0.5 mW/cm²	V_{CEsat}	150	150	160	180	mV
Stromverstärkung Current gain E_e = 0.5 mW/cm², V_{CE} = 5 V	$\frac{I_{PCE}}{I_{PCB}}$	170	270	420	670	–

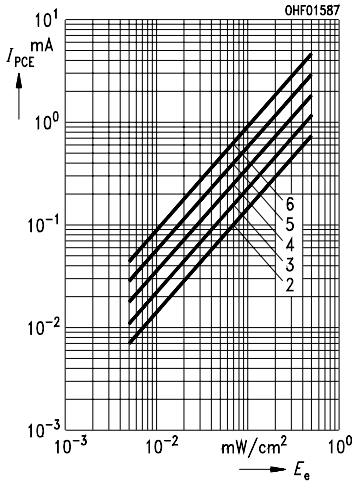
[1] I_{PCEmin} ist der minimale Fotostrom der jeweiligen Gruppe.

[1] I_{PCEmin} is the min. photocurrent of the specified group.

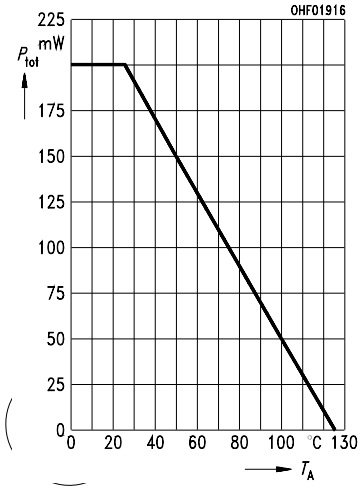
Relative Spectral sensitivity
$S_{rel} = f(\lambda)$



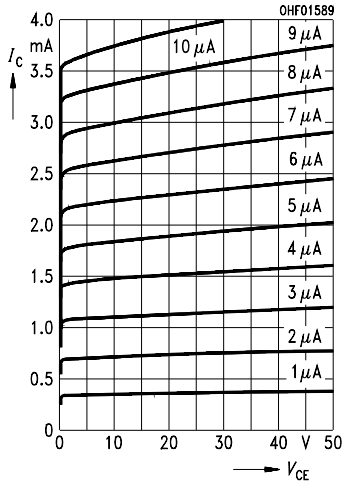
Photocurrent
$I_{PCE} = f(E_e)$, $V_{CE} = 5$ V



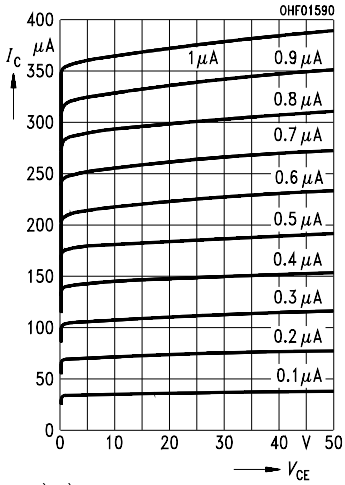
Total Power Dissipation
$P_{tot} = f(T_A)$



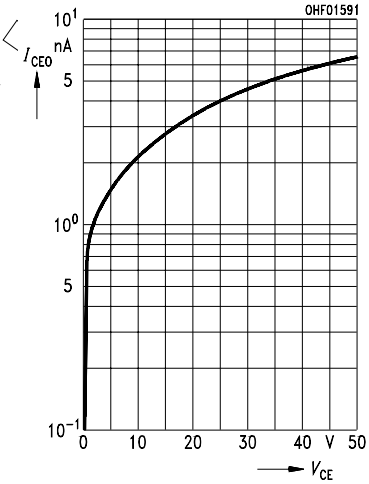
Output Characteristics
$I_C = f(V_{CE})$, I_B = Parameter



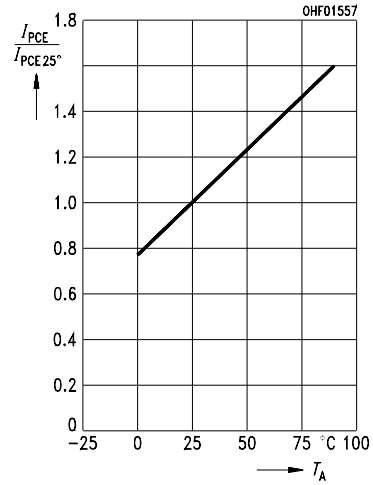
Output Characteristics
$I_C = f(V_{CE})$, I_B = Parameter



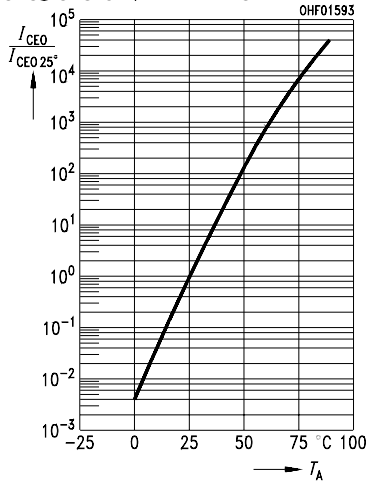
Dark Current
$I_{CEO} = f(V_{CE})$, $E = 0$



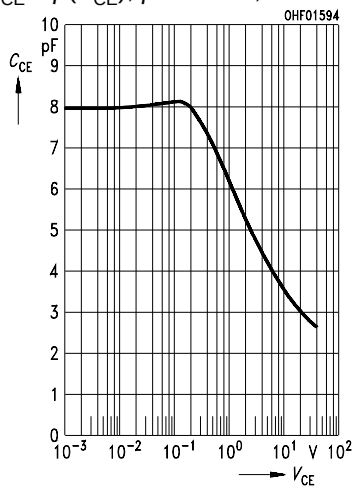
Photocurrent
$I_{PCE}/I_{PCE25^\circ} = f(T_A)$, $V_{CE} = 5$ V



Dark Current
$I_{CEO}/I_{CEO25^\circ} = f(T_A)$, $V_{CE} = 25$ V, $E = 0$

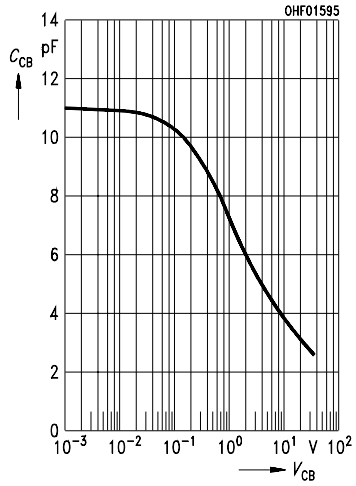


Collector-Emitter Capacitance
$C_{CE} = f(V_{CE})$, $f = 1$ MHz, $E = 0$



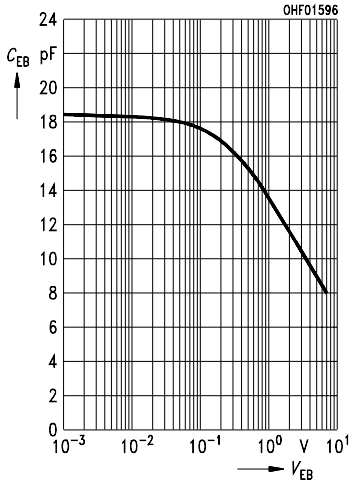
Collector-Base Capacitance

$C_{CB} = f(V_{CB})$, f = 1 MHz, E = 0



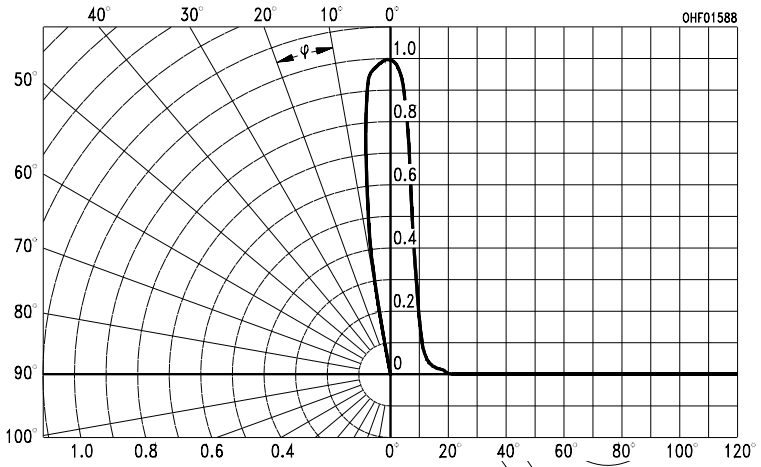
Emitter-Base Capacitance

$C_{EB} = f(V_{EB})$, f = 1 MHz, E = 0

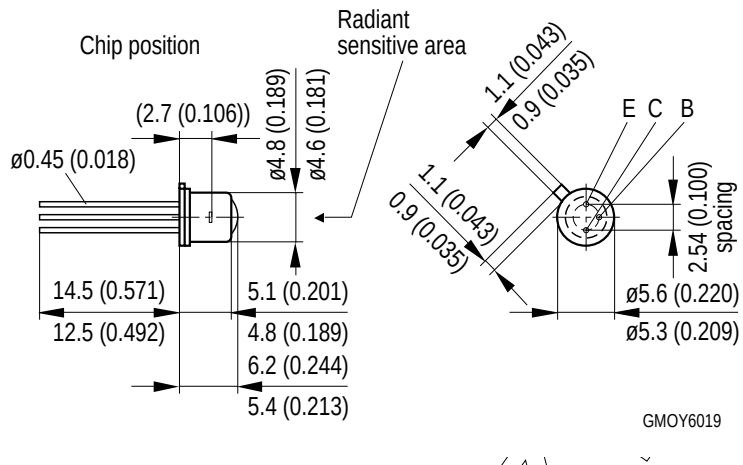


Directional Characteristics

$S_{rel} = f(\varphi)$



Maßzeichnung
Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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